

PSMN3R3-80ES

N-channel 80 V, 3.3 mΩ standard level MOSFET in I2PAK

Rev. 1 — 31 October 2011 Product data sheet

1. Product profile

1.1 General description

Standard level N-channel MOSFET in I2PAK package qualified to 175C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive

1.3 Applications

- DC-to-DC converters
- Load switch
- Motor control
- Server power supplies

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C		-	-	80	V
I_D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see Figure 1	[1]	-	-	120	A
P_{tot}	total power dissipation	T_{mb} = 25 °C; see Figure 2		-	-	338	W
T_j	junction temperature			-55	-	175	°C
Static characteristics							
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 100 °C; see Figure 12		-	4.6	5.4	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; see Figure 13	[2]	-	2.8	3.3	mΩ
Dynamic characteristics							
Q_{GD}	gate-drain charge	V_{GS} = 10 V; I_D = 75 A; V_{DS} = 40 V; see Figure 14; see Figure 15		-	27	-	nC
$Q_{G(tot)}$	total gate charge			-	139	-	nC
Avalanche ruggedness							
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 120 A; $V_{sup} \leq 80$ V; R_{GS} = 50 Ω; unclamped		-	-	676	mJ

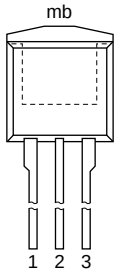
[1] Continuous current is limited by package.

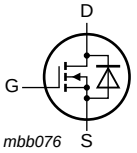
[2] Measured 3 mm from package.

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain		
3	S	source		
mb	D	drain		





SOT226 (I2PAK)

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN3R3-80ES	I2PAK	plastic single-ended package (I2PAK); TO-262	SOT226

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C		-	80	V
V_{DGR}	drain-gate voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C; R_{GS} = 20 kΩ		-	80	V
V_{GS}	gate-source voltage			-20	20	V
I_D	drain current	V_{GS} = 10 V; T_{mb} = 100 °C; see Figure 1	[1]	-	120	A
		V_{GS} = 10 V; T_{mb} = 25 °C; see Figure 1	[1]	-	120	A
I_{DM}	peak drain current	pulsed; $t_p \leq 10$ µs; T_{mb} = 25 °C; see Figure 3		-	830	A
P_{tot}	total power dissipation	T_{mb} = 25 °C; see Figure 2		-	338	W
T_{stg}	storage temperature			-55	175	°C
T_j	junction temperature			-55	175	°C
$T_{sld(M)}$	peak soldering temperature			-	260	°C
Source-drain diode						
I_S	source current	T_{mb} = 25 °C	[1]	-	120	A
I_{SM}	peak source current	pulsed; $t_p \leq 10$ µs; T_{mb} = 25 °C		-	830	A
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 120 A; $V_{sup} \leq 80$ V; R_{GS} = 50 Ω; unclamped		-	676	mJ

[1] Continuous current is limited by package.

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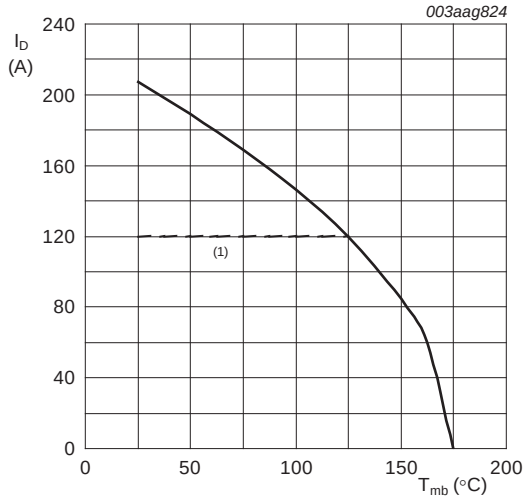
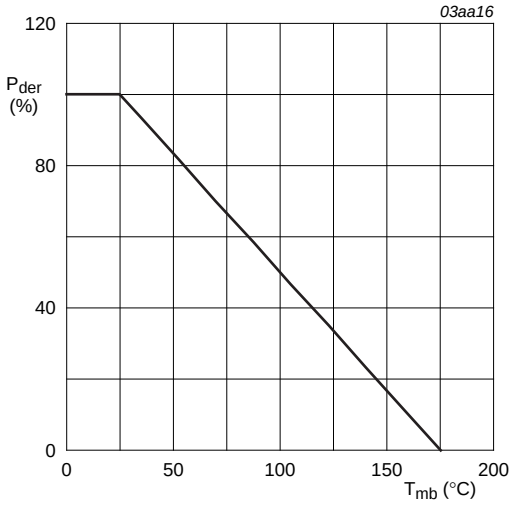


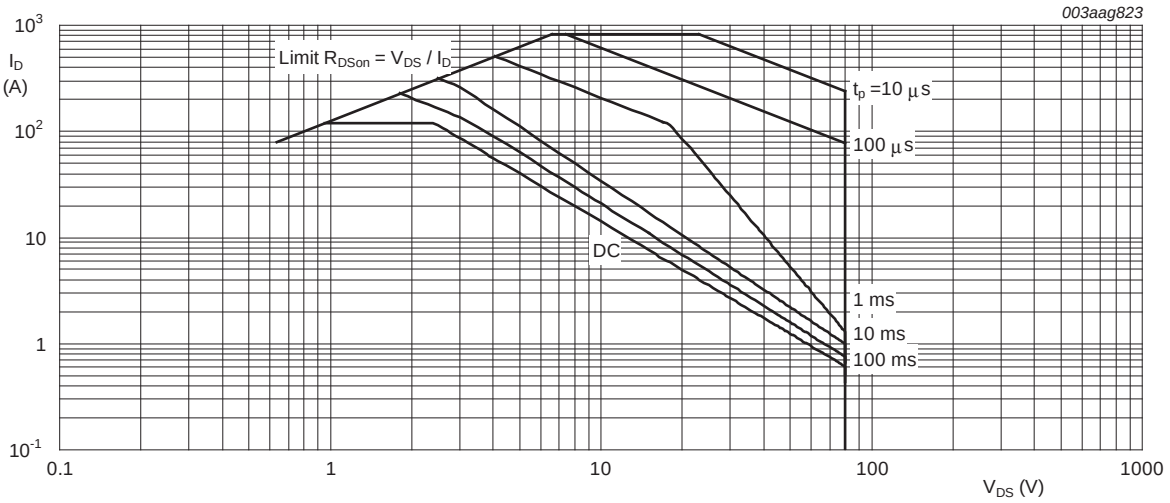
$V_{GS} \geq 10\,V$; (1) Capped at 120A due to package

Fig 1. Continuous drain current as a function of mounting base temperature



$$P_{der} = \frac{P_{tot}}{P_{tot(25°C)}} \times 100\,\%$$

Fig 2. Normalized total power dissipation as a function of mounting base temperature



$T_{mb} = 25\ °C$; I_{DM} is a single pulse; Capped at 120 A due to package

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

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5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j\text{-}mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.22	0.44	K/W
$R_{th(j\text{-}a)}$	thermal resistance from junction to ambient	Vertical in free air	-	60	-	K/W

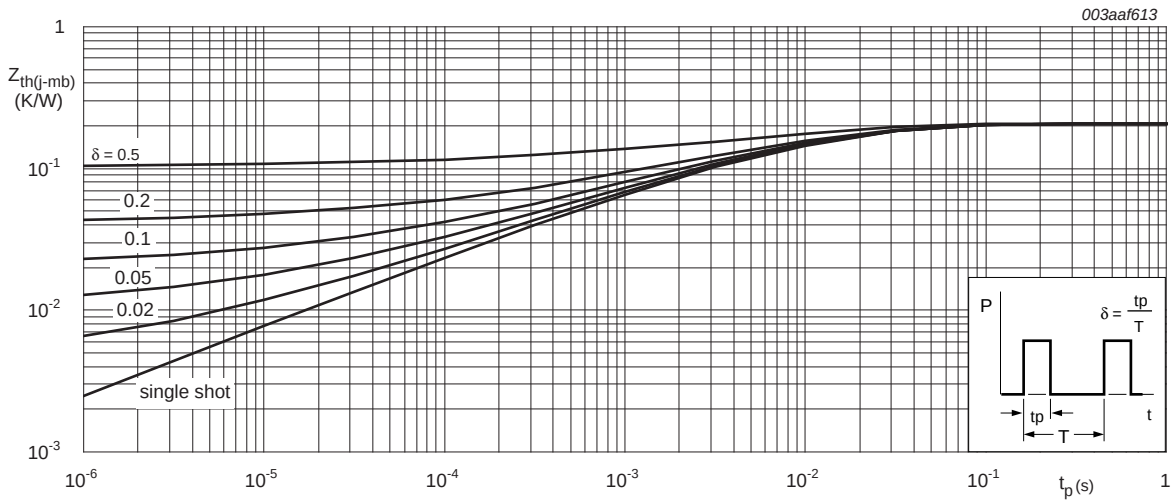

Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

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6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C		73	-	-	V
		I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C		80	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS}; T_j = 175 °C; see Figure 10		1	-	-	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = -55 °C; see Figure 10		-	-	4.6	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = 25 °C; see Figure 10; see Figure 11		2	3	4	V
I_{DSS}	drain leakage current	V_{DS} = 80 V; V_{GS} = 0 V; T_j = 25 °C		-	0.02	10	µA
		V_{DS} = 80 V; V_{GS} = 0 V; T_j = 175 °C		-	-	500	µA
I_{GSS}	gate leakage current	V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C		-	-	100	nA
		V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C		-	-	100	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 175 °C; see Figure 12		-	6.7	7.9	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 100 °C; see Figure 12		-	4.6	5.4	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; see Figure 13	[1]	-	2.8	3.3	mΩ
R_G	internal gate resistance (AC)	f = 1 MHz		-	0.9	-	Ω
Dynamic characteristics							
$Q_{G(tot)}$	total gate charge	I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V		-	135	-	nC
		I_D = 75 A; V_{DS} = 40 V; V_{GS} = 10 V; see Figure 14; see Figure 15		-	139	-	nC
Q_{GS}	gate-source charge			-	51	-	nC
$Q_{GS(th)}$	pre-threshold gate-source charge			-	30	-	nC
$Q_{GS(th-pl)}$	post-threshold gate-source charge			-	21	-	nC
Q_{GD}	gate-drain charge			-	27	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	I_D = 25 A; V_{DS} = 40 V; see Figure 14; see Figure 15		-	5.8	-	V
C_{iss}	input capacitance	V_{DS} = 40 V; V_{GS} = 0 V; f = 1 MHz; T_j = 25 °C; see Figure 16		-	9961	-	pF
C_{oss}	output capacitance			-	847	-	pF
C_{rss}	reverse transfer capacitance			-	401	-	pF
$t_{d(on)}$	turn-on delay time	V_{DS} = 40 V; R_L = 0.53 Ω; V_{GS} = 10 V; $R_{G(ext)}$ = 10 Ω; I_D = 75 A		-	41	-	ns
t_r	rise time			-	43	-	ns
$t_{d(off)}$	turn-off delay time			-	109	-	ns
t_f	fall time			-	44	-	ns

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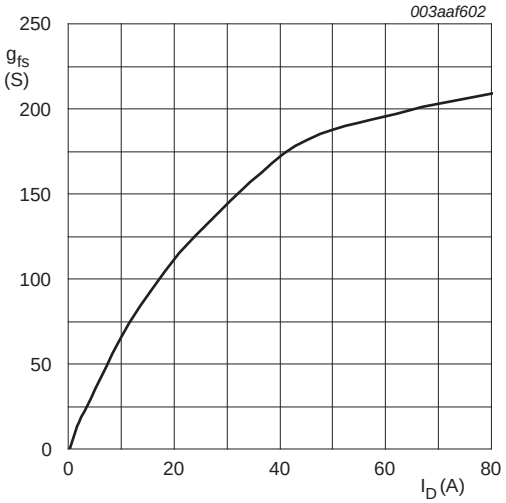
Table 6. Characteristics *...continued*

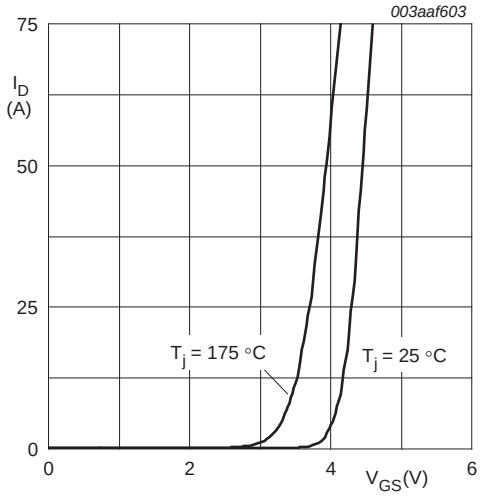
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Source-drain diode						
V_{SD}	source-drain voltage	I_S = 25 A; V_{GS} = 0 V; T_j = 25 °C; see Figure 17	-	0.8	1.2	V
t_{rr}	reverse recovery time	I_S = 25 A; dI_S/dt = 100 A/µs; V_{GS} = 0 V; V_{DS} = 20 V	-	63	-	ns
Q_r	recovered charge		-	121	-	nC

[1] Measured 3 mm from package.



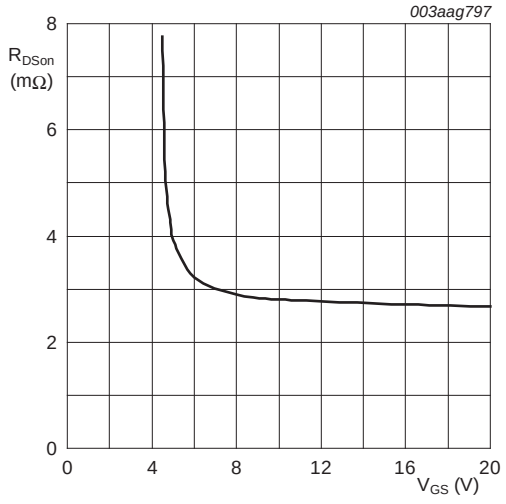
$T_j = 25\,°C; V_{DS} = 25V$

Fig 5. Forward transconductance as a function of drain current; typical values



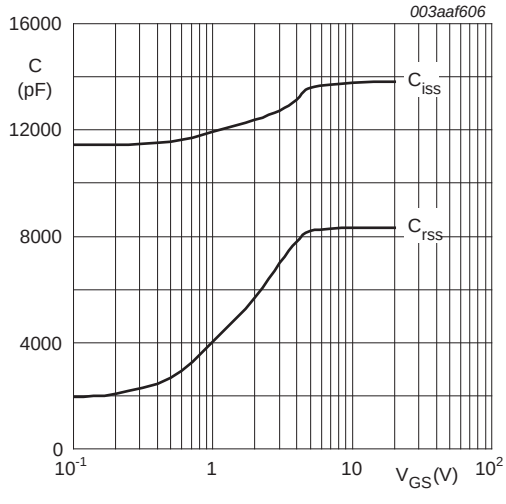
$V_{DS} > I_D \times R_{DSon}$

Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values



$T_j = 25\,°C;\ I_D = 25A$

Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values



$V_{DS} = 0V; f = 1MHz$

Fig 8. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

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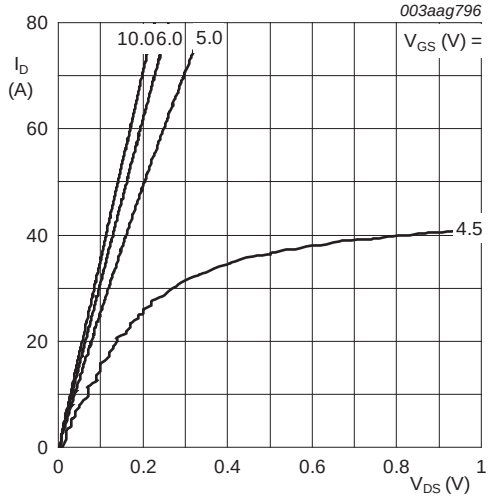
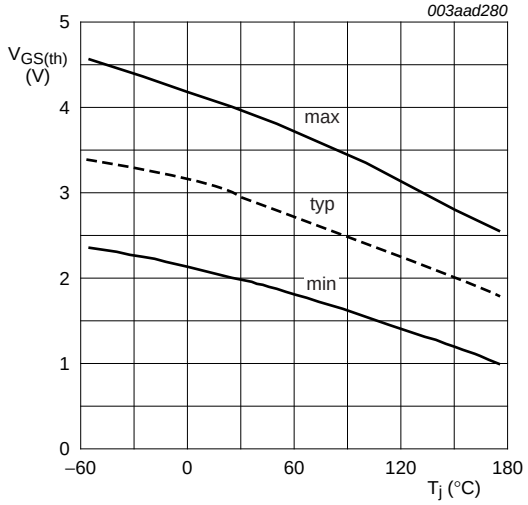


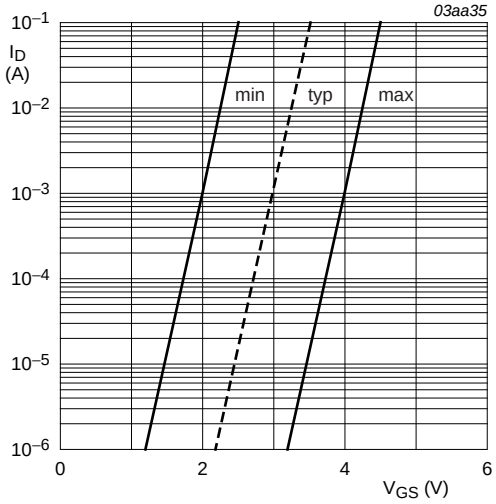
$T_j = 25°C$

Fig 9. Output characteristics; drain current as a function of drain-source voltage; typical values



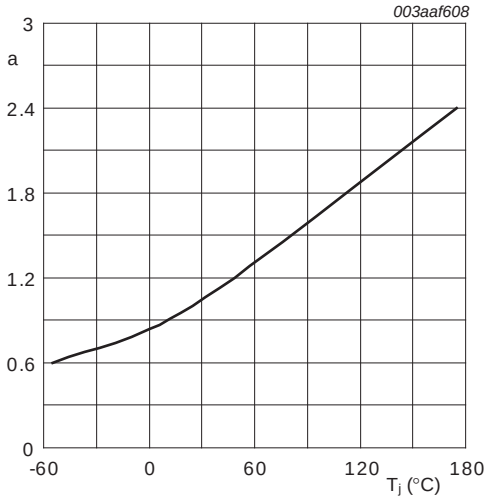
$I_D = 1\ \text{mA};\ V_{DS} = V_{GS}$

Fig 10. Gate-source threshold voltage as a function of junction temperature



$T_j = 25\,°C; V_{DS} = 5V$

Fig 11. Sub-threshold drain current as a function of gate-source voltage



$$a = \frac{R_{DSon}}{R_{DSon(25°C)}}$$

Fig 12. Normailzed drain-source on-state resistance factor as a function of junction temperature

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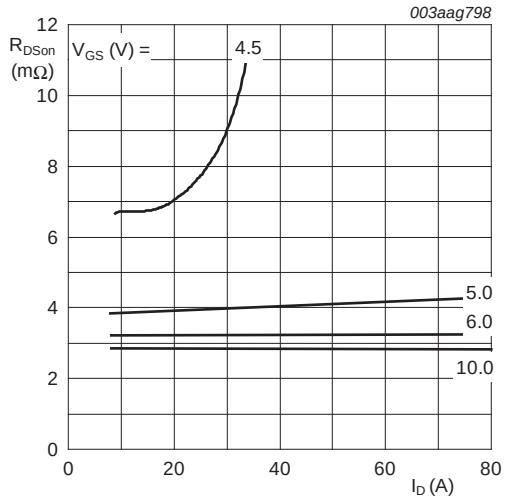


$T_j = 25°C$

Fig 13. Drain-source on-state resistance as a function of drain current; typical values

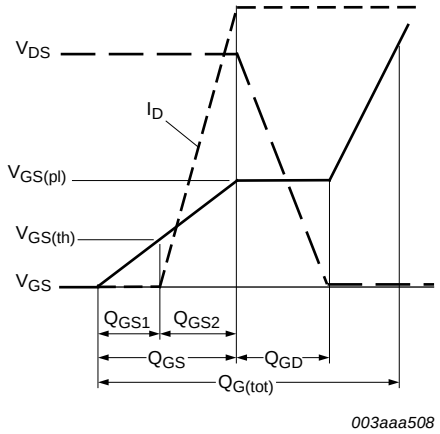
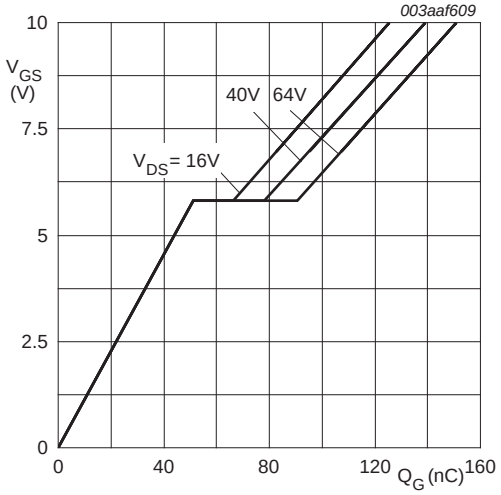
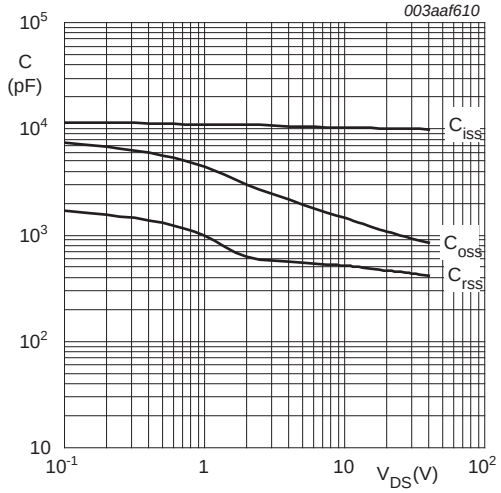


Fig 14. Gate charge waveform definitions



$T_j = 25\ °C; I_D = 75\ A$

Fig 15. Gate-source voltage as a function of gate charge; typical values



$V_{GS} = 0V; f = 1MHz$

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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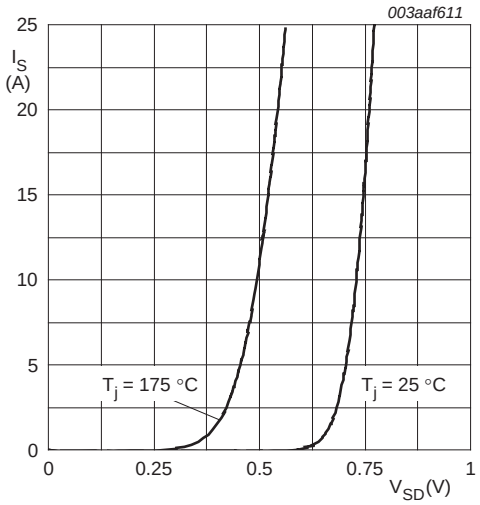

$V_{GS} = 0\,V$

Fig 17. Source current as a function of source-drain voltage; typical values

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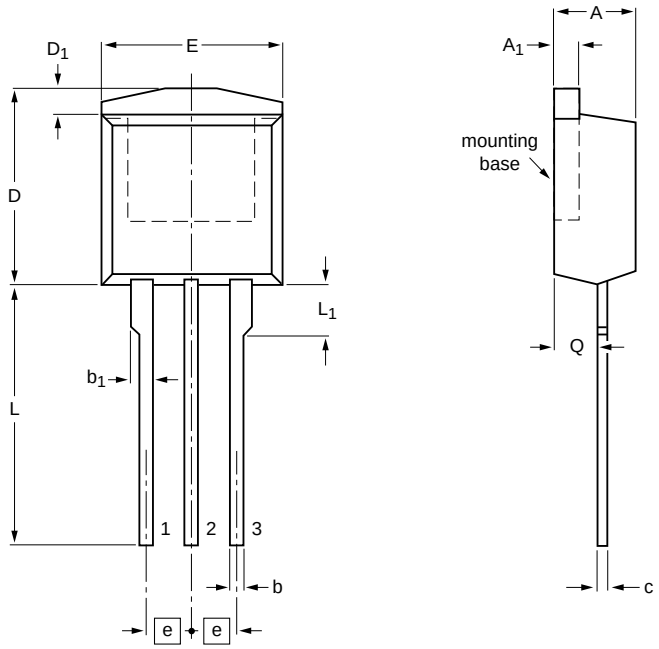
7. Package outline

Plastic single-ended package (I2PAK); low-profile 3-lead TO-262 **SOT226**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	b	b_1	c	D max	D_1	E	e	L	L_1	Q
mm	4.5 4.1	1.40 1.27	0.85 0.60	1.3 1.0	0.7 0.4	11	1.6 1.2	10.3 9.7	2.54	15.0 13.5	3.30 2.79	2.6 2.2

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT226		TO-262				~~06-02-14~~ 09-08-25

Fig 18. Package outline SOT226 (I2PAK)

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN3R3-80ES v.1	20111031	Product data sheet	-	-

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9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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10. Contact information

For more information, please visit: http://www.nxp.com

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